

ABSTRACT OF THE DISCLOSURE

A CCD type solid state image pickup device having: a number of photoelectric conversion elements formed in and on the semiconductor substrate in a matrix configuration of rows and columns; a plurality of 5 VCCDs each having a vertical channel region formed along each column of the photoelectric conversion elements, and charge transfer electrodes formed above the vertical channel region; an HCCD having a horizontal channel region coupled to one ends of the VCCDs, and charge transfer electrodes formed above the horizontal channel region; 10 a floating diffusion formed in the semiconductor substrate and coupled to one end of the HCCD; and an input gate electrode of an output amplifier having a portion extending at least near to the floating diffusion, and the input gate electrode being thinner than the charge transfer electrodes.